MC14532B

8-Bit Priority Encoder

The MC14532B is constructed with complementary MOS (CMOS) enhancement mode devices. The primary function of a priority encoder is to provide a binary address for the active input with the highest priority. Eight data inputs (D0 thru D7) and an enable input (E_{in}) are provided. Five outputs are available, three are address outputs (Q0 thru Q2), one group select (GS) and one enable output (E_{out}).

Features

- Diode Protection on All Inputs
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Capable of Driving Two Low−Power TTL Loads or One Low−Power Schottky TTL Load over the Rated Temperature Range
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
- This Device is Pb−Free and is RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Rating	Symbol	Value	Unit
DC Supply Voltage Range	V_{DD}	−0.5 to +18.0	V
Input or Output Voltage Range (DC or Transient)	V_{in}, V_{out}	−0.5 to V_{DD} + 0.5	V
Input or Output Current (DC or Transient) per Pin	I_{in}, I_{out}	±10	mA
Power Dissipation, per Package (Note 1)	P_D	500	mW
Ambient Temperature Range	T_A	−55 to +125	°C
Storage Temperature Range	T_{stg}	−65 to +150	°C
Lead Temperature (8 Sec Soldering)	T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: “D/DW” Package: –7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high−impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

TRUTH TABLE

Input									Output				
E_{in}	D7	D6	D5	D4	D3	D2	D1	D0	GS	Q2	Q1	Q0	E_{out}
0	X	X	X	X	X	X	X	X	0	0	0	0	0
1	0	0	0	0	0	0	0	0	0	0	0	0	1
1	1	X	X	X	X	X	X	X	1	1	1	1	0
1	0	1	X	X	X	X	X	X	1	1	1	0	0
1	0	0	1	X	X	X	X	X	1	1	0	1	0
1	0	0	0	1	X	X	X	X	1	1	0	0	0
1	0	0	0	0	1	X	X	X	1	0	1	1	0
1	0	0	0	0	0	1	X	X	1	0	1	0	0
1	0	0	0	0	0	0	1	X	1	0	0	1	0
1	0	0	0	0	0	0	0	1	1	0	0	0	0

X = Don’t Care

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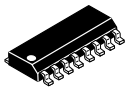

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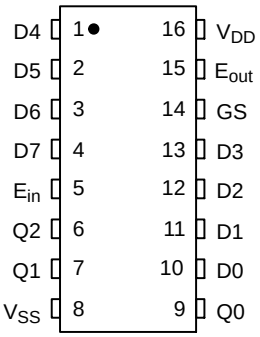
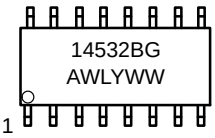
SOIC−16
D SUFFIX
CASE 751B

PIN ASSIGNMENT



MARKING DIAGRAM



A = Assembly Location
WL = Wafer Lot
YY, Y = Year
WW = Work Week
G = Pb−Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ORDERING INFORMATION

Device	Package	Shipping†
MC14532BDG	SOIC−16 (Pb−Free)	48 Units / Rail
MC14532BDR2G	SOIC−16 (Pb−Free)	2500 / Tape & Reel
NLV14532BDR2G*	SOIC−16 (Pb−Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	− 55°C Min	− 55°C Max	25°C Min	25°C Typ (Note 2)	25°C Max	125°C Min	125°C Max	Unit
Output Voltage “0” Level V_{in} = V_{DD} or 0	V_{OL}	5.0	−	0.05	−	0	0.05	−	0.05	Vdc
		10	−	0.05	−	0	0.05	−	0.05	
		15	−	0.05	−	0	0.05	−	0.05	
“1” Level V_{in} = 0 or V_{DD}	V_{OH}	5.0	4.95	−	4.95	5.0	−	4.95	−	Vdc
		10	9.95	−	9.95	10	−	9.95	−	
		15	14.95	−	14.95	15	−	14.95	−	
Input Voltage “0” Level	V_{IL}									Vdc
(V_O = 4.5 or 0.5 Vdc)		5.0	−	1.5	−	2.25	1.5	−	1.5	
(V_O = 9.0 or 1.0 Vdc)		10	−	3.0	−	4.50	3.0	−	3.0	
(V_O = 13.5 or 1.5 Vdc)		15	−	4.0	−	6.75	4.0	−	4.0	
“1” Level	V_{IH}									Vdc
(V_O = 0.5 or 4.5 Vdc)		5.0	3.5	−	3.5	2.75	−	3.5	−	
(V_O = 1.0 or 9.0 Vdc)		10	7.0	−	7.0	5.50	−	7.0	−	
(V_O = 1.5 or 13.5 Vdc)		15	11	−	11	8.25	−	11	−	
Output Drive Current	I_{OH}									mAdc
(V_{OH} = 2.5 Vdc) Source		5.0	–3.0	−	–2.4	–4.2	−	–1.7	−	
(V_{OH} = 4.6 Vdc)		5.0	–0.64	−	– 0.51	–0.88	−	–0.36	−	
(V_{OH} = 9.5 Vdc)		10	–1.6	−	–1.3	–2.25	−	–0.9	−	
(V_{OH} = 13.5 Vdc)		15	–4.2	−	–3.4	–8.8	−	–2.4	−	
(V_{OL} = 0.4 Vdc) Sink	I_{OL}	5.0	0.64	−	0.51	0.88	−	0.36	−	mAdc
(V_{OL} = 0.5 Vdc)		10	1.6	−	1.3	2.25	−	0.9	−	
(V_{OL} = 1.5 Vdc)		15	4.2	−	3.4	8.8	−	2.4	−	
Input Current	I_{in}	15	−	±0.1	−	±0.00001	±0.1	−	±1.0	μAdc
Input Capacitance (V_{in} = 0)	C_{in}	−	−	−	−	5.0	7.5	−	−	pF
Quiescent Current (Per Package)	I_{DD}	5.0	−	5.0	−	0.005	5.0	−	150	μAdc
		10	−	10	−	0.010	10	−	300	
		15	−	20	−	0.015	20	−	600	
Total Supply Current (Notes 3, 4) (Dynamic plus Quiescent, Per Package) (C_L = 50 pF on all outputs, all buffers switching)	I_T	5.0	I_T = (1.74 μA/kHz) f + I_{DD}							μAdc
		10	I_T = (3.65 μA/kHz) f + I_{DD}							
		15	I_T = (5.73 μA/kHz) f + I_{DD}							

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.
3. The formulas given are for the typical characteristics only at 25°C.
4. To calculate total supply current at loads other than 50 pF:

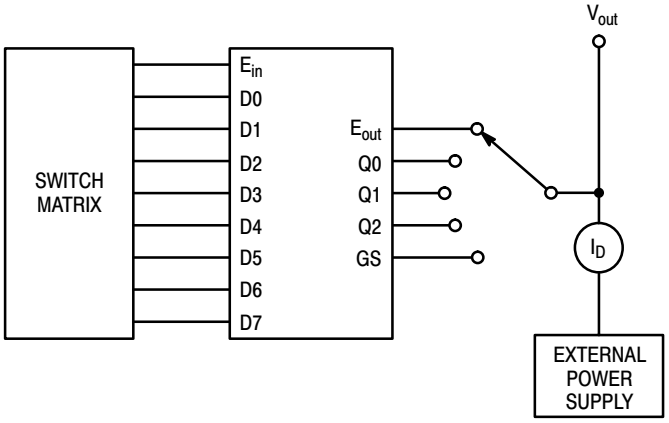
$$I_T(C_L) = I_T(50\ pF) + (C_L - 50)\ Vfk$$

where: I_T is in μA (per package), C_L in pF, V = (V_{DD} – V_{SS}) in volts, f in kHz is input frequency, and k = 0.005.

SWITCHING CHARACTERISTICS (C_L = 50 pF, T_A = 25°C) (Note 5)

Characteristic	Symbol	V_{DD}	Min	Typ (Note 6)	Max	Unit
Output Rise and Fall Time t_{TLH}, t_{THL} = (1.5 ns/pF) C_L + 25 ns t_{TLH}, t_{THL} = (0.75 ns/pF) C_L + 12.5 ns t_{TLH}, t_{THL} = (0.55 ns/pF) C_L + 9.5 ns	t_{TLH}, t_{THL}	 5.0 10 15	 – – –	 100 50 40	 200 100 80	ns
Propagation Delay Time — E_{in} to E_{out} t_{PLH}, t_{PHL} = (1.7 ns/pF) C_L + 120 ns t_{PLH}, t_{PHL} = (0.66 ns/pF) C_L + 77 ns t_{PLH}, t_{PHL} = (0.5 ns/pF) C_L + 55 ns	t_{PLH}, t_{PHL}	 5.0 10 15	 – – –	 205 110 80	 410 220 160	ns
Propagation Delay Time — E_{in} to GS t_{PLH}, t_{PHL} = (1.7 ns/pF) C_L + 90 ns t_{PLH}, t_{PHL} = (0.66 ns/pF) C_L 57 ns t_{PLH}, t_{PHL} = (0.5 ns/pF) C_L + 40 ns	t_{PLH}, t_{PHL}	 5.0 10 15	 – – –	 175 90 65	 350 180 130	ns
Propagation Delay Time — E_{in} to Q_n t_{PLH}, t_{PHL} = (1.7 ns/pF) C_L + 195 ns t_{PLH}, t_{PHL} = (0.66 ns/pF) C_L + 107 ns t_{PLH}, t_{PHL} = (0.5 ns/pF) C_L + 75 ns	t_{PHL}, t_{PLH}	 5.0 10 15	 – – –	 280 140 100	 560 280 200	ns
Propagation Delay Time — D_n to Q_n t_{PLH}, t_{PHL} = (1.7 ns/pF) C_L + 265 ns t_{PLH}, t_{PHL} = (0.66 ns/pF) C_L + 137 ns t_{PLH}, t_{PHL} = (0.5 ns/pF) C_L + 85 ns	t_{PLH}, t_{PHL}	 5.0 10 15	 – – –	 300 170 110	 600 340 220	ns
Propagation Delay Time — D_n to GS t_{PLH}, t_{PHL} = (1.7 ns/pF) C_L + 195 ns t_{PLH}, t_{PHL} = (0.66 ns/pF) C_L + 107 ns t_{PLH}, t_{PHL} = (0.5 ns/pF) C_L + 75 ns	t_{PLH}, t_{PHL}	 5.0 10 15	 – – –	 280 140 100	 560 280 200	ns

5. The formulas given are for the typical characteristics only at 25°C.
6. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.



Output Under Test	$V_{GS} = V_{DD}$, $V_{DS} = V_{out}$ Sink Current		$V_{GS} = -V_{DD}$, $V_{DS} = V_{out} - V_{DD}$ Source Current		
	D0 thru D7	E_{in}	D0 thru D6	D7	E_{in}
E_{out}	X	0	0	0	1
Q0	X	0	0	1	1
Q1	X	0	0	1	1
Q2	X	0	0	1	1
GS	X	0	0	1	1

Figure 1. Typical Sink and Source Current Characteristics

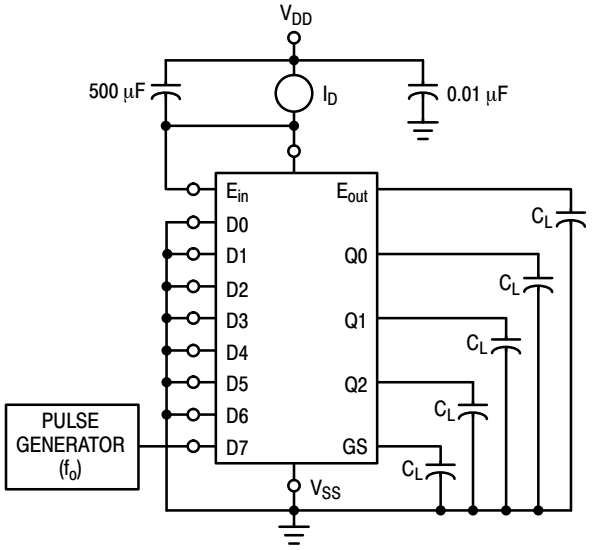
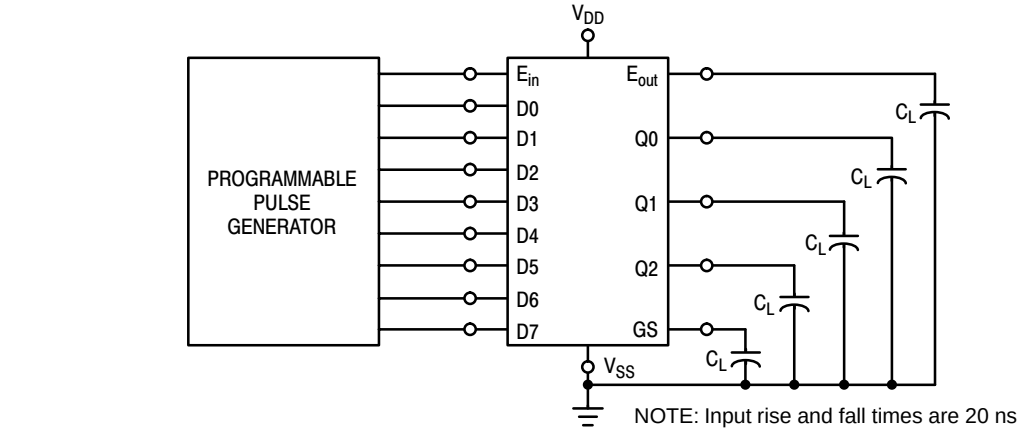


Figure 2. Typical Power Dissipation Test Circuit



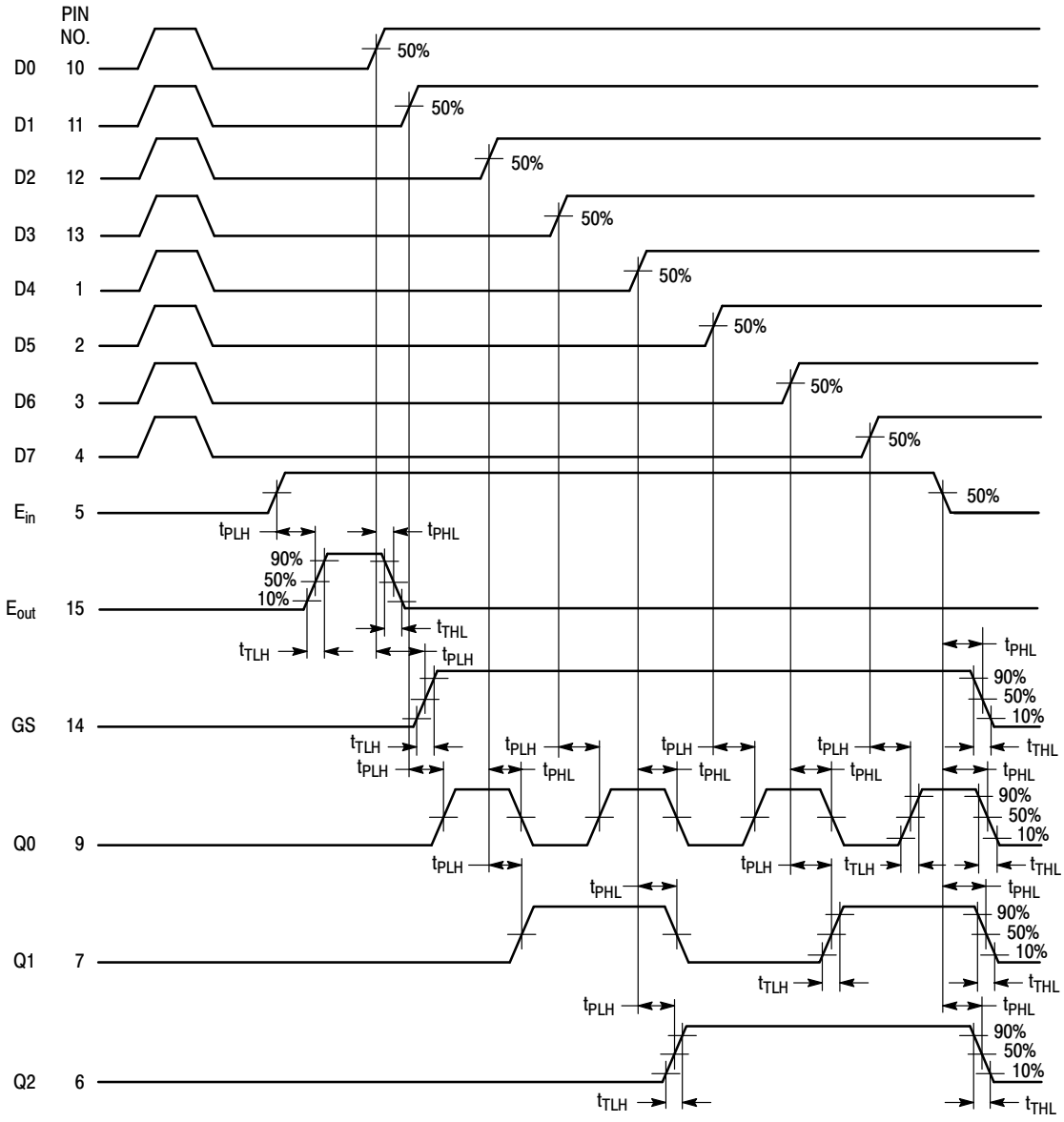


Figure 3. AC Test Circuit and Waveforms

LOGIC EQUATIONS

$E_{out} = E_{in} \bullet \overline{D0} \bullet \overline{D1} \bullet \overline{D2} \bullet \overline{D3} \bullet \overline{D4} \bullet \overline{D5} \bullet \overline{D6} \bullet \overline{D7}$

$Q0 = E_{in} \bullet (D1 \bullet \overline{D2} \bullet \overline{D4} \bullet \overline{D6} + D3 \bullet \overline{D4} \bullet \overline{D6} + D5 \bullet \overline{D6} + D7)$

$Q1 = E_{in} \bullet (D2 \bullet \overline{D4} \bullet \overline{D5} + D3 \bullet \overline{D4} \bullet \overline{D5} + D6 + D7)$

$Q2 = E_{in} \bullet (D4 + D5 + D6 + D7)$

$GS = E_{in} \bullet (D0 + D1 + D2 + D3 + D4 + 05 + D6 + D7)$

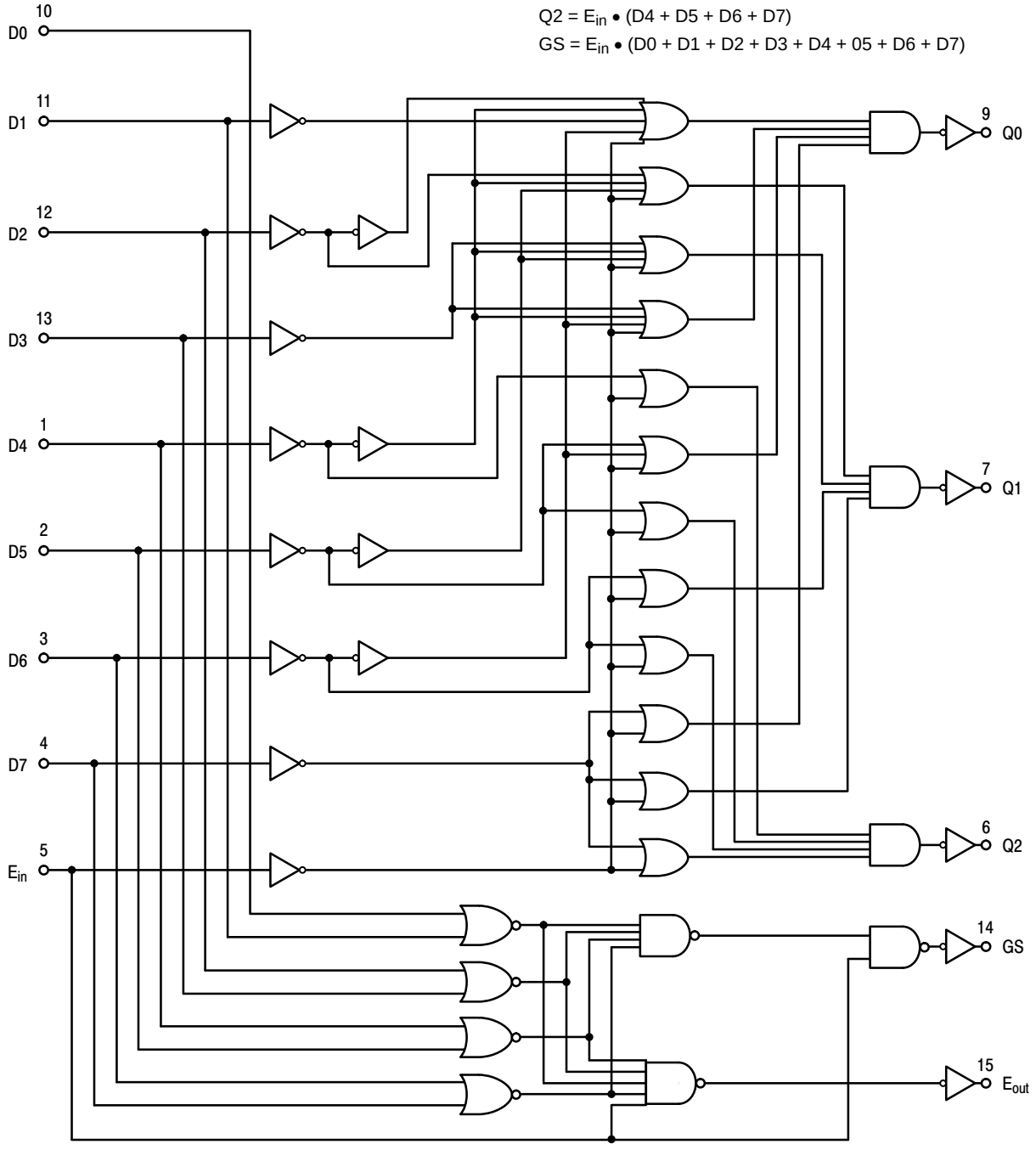


Figure 4. Logic Diagram
(Positive Logic)

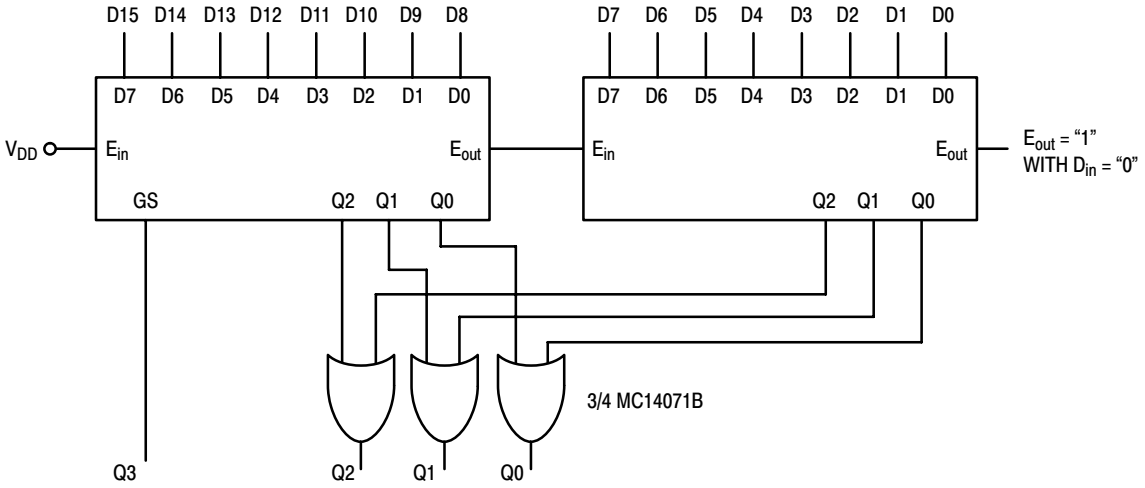


Figure 5. Two MC14532B's Cascaded for 4−Bit Output

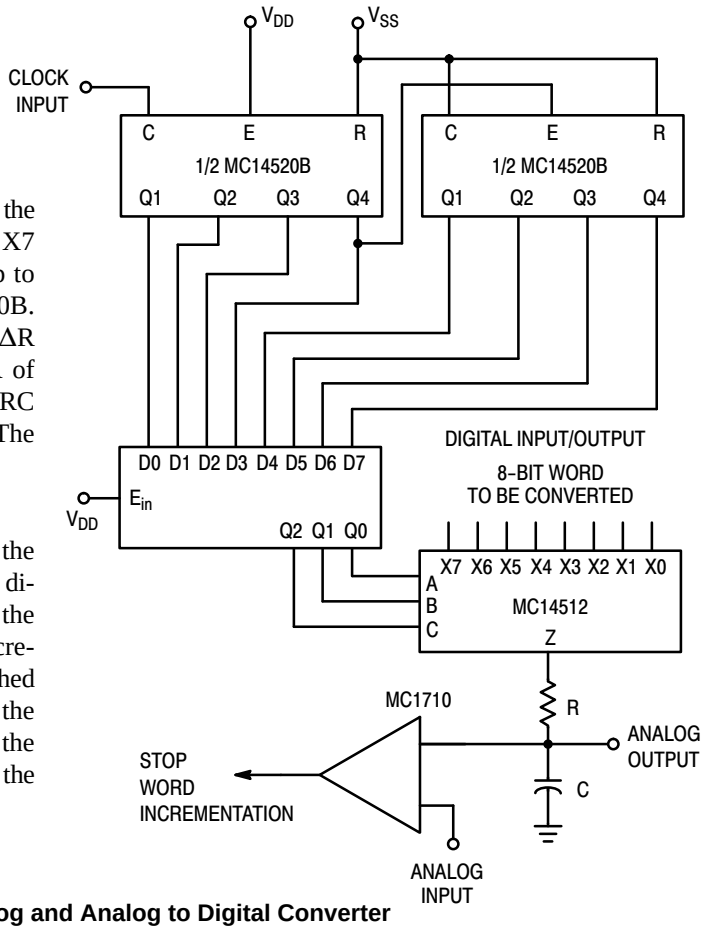


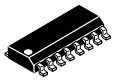
Figure 6. Digital to Analog and Analog to Digital Converter

DIGITAL TO ANALOG CONVERSION

The digital eight−bit word to be converted is applied to the inputs of the MC14512 with the most significant bit at X7 and the least significant bit at X0. A clock input of up to 2.5 MHz (at V_{DD} = 10 V) is applied to the MC14520B. A compromise between I_{bias} for the MC1710 and ΔR between N and P−channel outputs gives a value of R of 33 kΩ. In order to filter out the switching frequencies, RC should be about 1.0 ms (if R = 33 kΩ, C ≈ 0.03 μF). The analog 3.0 dB bandwidth would then be dc to 1.0 kHz.

ANALOG TO DIGITAL CONVERSION

An analog signal is applied to the analog input of the MC1710. A digital eight−bit word known to represent a digitized level less than the analog input is applied to the MC14512 as in the D to A conversion. The word is incremented at rates sufficient to allow steady state to be reached between incrementations (i.e. 3.0 ms). The output of the MC1710 will change when the digital input represents the first digitized level above the analog input. This word is the digital representation of the analog word.



SCALE 1:1

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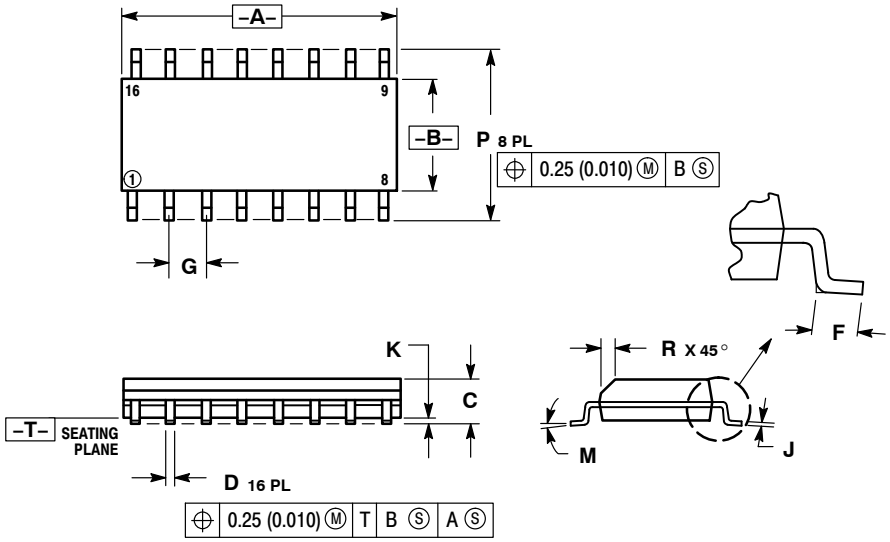
ISSUE K

DATE 29 DEC 2006



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

STYLE 1:
PIN 1. COLLECTOR
2. BASE
3. EMITTER
4. NO CONNECTION
5. EMITTER
6. BASE
7. COLLECTOR
8. COLLECTOR
9. BASE
10. EMITTER
11. NO CONNECTION
12. EMITTER
13. BASE
14. COLLECTOR
15. EMITTER
16. COLLECTOR

STYLE 2:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION
4. CATHODE
5. CATHODE
6. NO CONNECTION
7. ANODE
8. CATHODE
9. CATHODE
10. ANODE
11. NO CONNECTION
12. CATHODE
13. CATHODE
14. NO CONNECTION
15. ANODE
16. CATHODE

STYLE 3:
PIN 1. COLLECTOR, DYE #1
2. BASE, #1
3. EMITTER, #1
4. COLLECTOR, #1
5. COLLECTOR, #2
6. BASE, #2
7. EMITTER, #2
8. COLLECTOR, #2
9. COLLECTOR, #3
10. BASE, #3
11. EMITTER, #3
12. COLLECTOR, #3
13. COLLECTOR, #4
14. BASE, #4
15. EMITTER, #4
16. COLLECTOR, #4

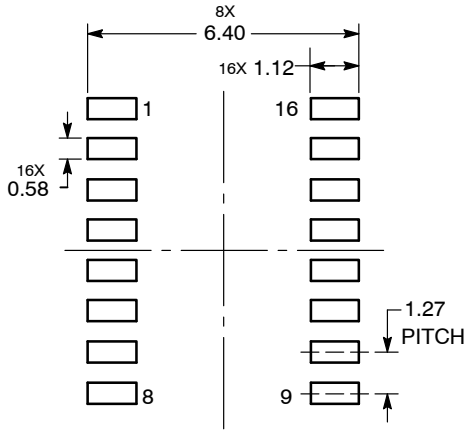
STYLE 4:
PIN 1. COLLECTOR, DYE #1
2. COLLECTOR, #1
3. COLLECTOR, #2
4. COLLECTOR, #2
5. COLLECTOR, #3
6. COLLECTOR, #3
7. COLLECTOR, #4
8. COLLECTOR, #4
9. BASE, #4
10. EMITTER, #4
11. BASE, #3
12. EMITTER, #3
13. BASE, #2
14. EMITTER, #2
15. BASE, #1
16. EMITTER, #1

STYLE 5:
PIN 1. DRAIN, DYE #1
2. DRAIN, #1
3. DRAIN, #2
4. DRAIN, #2
5. DRAIN, #3
6. DRAIN, #3
7. DRAIN, #4
8. DRAIN, #4
9. GATE, #4
10. SOURCE, #4
11. GATE, #3
12. SOURCE, #3
13. GATE, #2
14. SOURCE, #2
15. GATE, #1
16. SOURCE, #1

STYLE 6:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. CATHODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE
15. ANODE
16. ANODE

STYLE 7:
PIN 1. SOURCE N-CH
2. COMMON DRAIN (OUTPUT)
3. COMMON DRAIN (OUTPUT)
4. GATE P-CH
5. COMMON DRAIN (OUTPUT)
6. COMMON DRAIN (OUTPUT)
7. COMMON DRAIN (OUTPUT)
8. SOURCE P-CH
9. SOURCE P-CH
10. COMMON DRAIN (OUTPUT)
11. COMMON DRAIN (OUTPUT)
12. COMMON DRAIN (OUTPUT)
13. GATE N-CH
14. COMMON DRAIN (OUTPUT)
15. COMMON DRAIN (OUTPUT)
16. SOURCE N-CH

SOLDERING FOOTPRINT



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Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

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